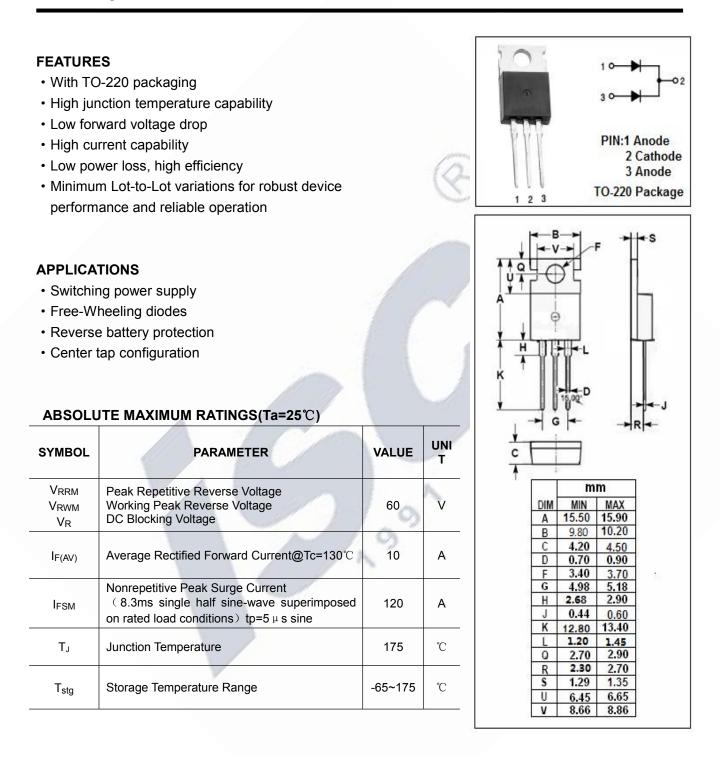


INCHANGE SEMICONDUCTOR

Schottky Barrier Rectifier

SBR1060CT



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SBR1060CT

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	2	°C/W

ELECTRICAL CHARACTERISTICS (Pulse Test: Pulse Width=300 µ s,Duty Cycle≤1%)

SYMBOL	PARAMETER	CONDITIONS	МАХ	UNIT
VF	Maximum Instantaneous Forward Voltage	I⊧= 5A ; Tc= 25°C	0.68	- V
		I _F = 5A ; Tc= 125 ℃	0.57	
IR	Maximum Instantaneous Reverse Current	V _R = V _{RWM;} Tc= 25 °C	0.5	mA
		V _R = V _{RWM;} Tc= 125℃	100	

NOTICE:

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2

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